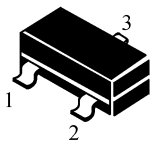
A

Excellent H_{FE} Linearity H_{FE} H_{FE}(0.1mA)/ h_{FE}(2mA)=0.95(Typ.)
High H_{FE} H_{FE} H_{FE}=200 700
Low Noise NF=1dB(Typ.),10dB(Max.).
Complementary to S9015(GM9015) GM9015)

SOT—23

1. BASE
2. EMITTER
3. COLLECTOR



A A (=25)

CHARACTERISTIC	Symbol	Rating	Unit
Collector-Base Voltage -	V_{CBO}	50	Vdc
Collector-Emitter Voltage -	V_{CEO}	45	Vdc
Emitter-Base Voltage -	V_{EBO}	5.0	Vdc
Collector Current-Continuous -	Ic	150	mAdc
Base Current	I_B	30	mAdc
Collector Power Dissipation	P_C	225	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

A

9014 = 6

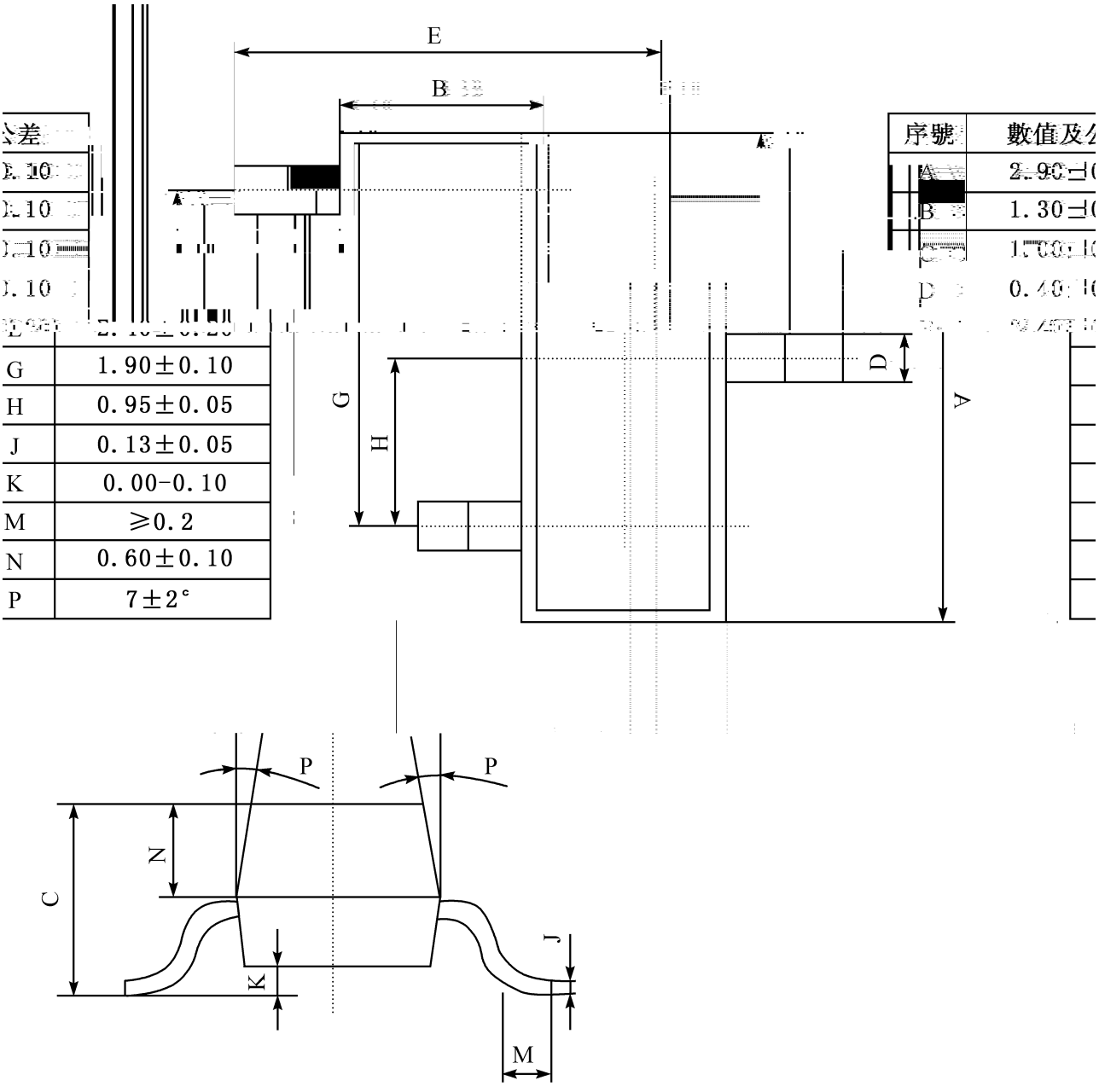
A A A

($_A$=25 25 **)**

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	V_{CB}=50V,I_E=0	—	—	0.1	A
Emitter Cutoff Current	I_{EBO}	V_{EB}=5V,I_C=0	—	—	0.1	A
Collector-Base Breakdown Voltage -	$V_{(BR)CBO}$	I_C=100 A	50	—	—	V
Collector-Emitter Breakdown Voltage -	$V_{(BR)CEO}$	I_C=1.0mA	45	—	—	V
Emitter-Base Breakdown Voltage -	$V_{(BR)EBO}$	I_E=100 A	5	—	—	V
DC Current Gain	h_{FE}	V_{CE}=6V,I_C=2mA	200	—	700	—
Collector-Emitter Saturation Voltage -	$V_{CE(sat)}$	I_C=100mA, I_B=5mA	—	—	0.3	V
Base-Emitter Voltage -	V_{BE}	V_{CE}=5.0V,I_C=10mA	—	—	0.82	V
Transition Frequency	f_T	V_{CE}=5.0V,I_C=10mA	100	180	—	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=10V,I_E=0, f=1MHz	—	4.0	7.0	pF

深圳市弗瑞鑫电子有限公司
工程专用章

外形封装尺寸



序號	數值及公
A	2.90±0
B	1.30±0
C	1.00±0
D	0.40±0

公差	
E	2.10±0.20
B	1.10±0.10
G	1.90±0.10
H	0.95±0.05
J	0.13±0.05
K	0.00-0.10
M	≥0.2
N	0.60±0.10
P	7±2°